

IN THE SPECIFICATION

Please replace the paragraph at page 2, lines 4-17, with the following rewritten paragraph:

Polycrystalline silicon has a ~~high~~ higher mobility of electrons or electron holes than the amorphous silicon. Therefore, when a transistor is formed by using polycrystalline silicon, since the switching speed is higher than that in the case of using amorphous silicon, there is an advantage that the response of a display becomes fast and the design margin of any other component can be reduced. Further, when peripheral circuits such as a driver circuit formed at a part other than a display main body or a DAC which converts a digital signal into an analog signal are formed within a display area, using the amorphous silicon enables high-speed operation of these peripheral circuits.

Please replace the paragraph at page 26, lines 4-24, with the following rewritten paragraph:

Therefore, as shown in FIG. 6, in regard to the light intensity distribution of the light beam transmitted through the phase shift mask 4 having a plurality of the basic unit parts, on the substrate 6, the light beam cyclically has the light intensity distribution of the inverse peak pattern, in which ~~has the~~ light intensity has a minimum peak value, e.g., substantially zero, at a point corresponding to each phase shift portion 4e of the phase shift mask 4 and rapidly increases as distanced from the phase shift portion 4e. That is, a minimum position of the cyclic ~~the~~ light intensity distribution of the inverse peak pattern is determined by the phase shift portion 4e. It is to be noted that the cyclic light intensity distribution of the inverse peak pattern has substantially the same profiles on both the x-z plane and the y-z plane. Further, a widthwise dimension of the light intensity distribution of the inverse peak

pattern varies in proportion to the  $1/2$  power of a distance (i.e., a defocus quantity) between the phase shift mask 4 and the substrate 6.

Please replace the paragraph at page 27, lines 11-26, with the following rewritten paragraph:

FIGS. 7A and 7B are views showing the light intensity distribution of the light beam transmitted through the transmission type amplitude modulation mask 1 and the phase shift mask 4 which can be obtained on the substrate 6. In the first embodiment, as described above, the transmission type amplitude modulation mask 1 has a function to subject the light beam that has the uniform light intensity distribution to amplitude modulation and convert it into a light beam which cyclically has a an upward concave light intensity distribution such as shown in FIG. 3B. On the other hand, the phase shift mask 4 has a function to convert a light beam that has a uniform light intensity distribution into a light beam which cyclically has the light intensity distribution of the inverse peak pattern such as shown in FIG. 6.

Please replace the paragraph at page 32, lines 4-16, with the following rewritten paragraph:

Therefore, in the first embodiment, it is preferable to form the phase shift surface of the phase shift mask 4 on the second image-forming optical system 5 side. In such a structure, since the first image-forming optical system 3 includes a glass substrate part of the phase shift mask 4, the image forming performance is readily lowered due to an influence of the aberration of the glass substrate part. However, since the second image-forming optical system 5 does not ~~includes~~ include the glass substrate part of the phase shift mask 4, it is possible to assure the high resolution and image forming performance without being affected by the aberration.

Please replace the paragraph at page 54, line 8 to page 55, line 3, with the following rewritten paragraph:

Then, the lateral growth starts from the crystal nucleus ~~long~~along the x direction where a light intensity gradient (i.e., a temperature gradient) is large. In the light intensity distribution of the two-stage inverse peak pattern, since a part where the light intensity decreases does not substantially exist in the intermediate portion, the lateral growth reaches a peak without stopping in mid course, thereby realizing growth of the large crystal. In particular, since an inflection point where the inclination decreases exists between the inverse peak pattern portion and the upward concave portion in the first embodiment, when the semiconductor film of the substrate 6 is irradiated with the light beam that has the light intensity distribution of the two-stage inverse peak pattern, crystallization is carried out in a wide area extending from the center of the light intensity distribution of the two-stage inverse peak pattern in the widthwise direction. Therefore, the monocrystalline can be generated with respect to each pixel by equalizing the widthwise direction of the light intensity distribution of the two-stage inverse peak pattern to a pixel pitch of the liquid crystal.

Please replace the paragraph at page 57, lines 6-18, with the following rewritten paragraph:

The transmission filter 15 includes an elongated rectangular central area 15a having ~~an~~a transmittance of, e.g., 50% and a pair of semicircular peripheral areas 15b which are formed so as to sandwich this central area 15a and have a transmittance of substantially 100%. A longitudinal direction of the central area 15a of this transmission filter 15 and a longitudinal direction of each minute cylindrical lens element 13'a of the micro cylindrical lens array 13' are set so as to be optically associated with each other. Although the central

area 15a is defined by substantially parallel chords, it is not restricted thereto, and any other shape may be adopted.

Please replace the paragraph at page 58, line 23 to page 59, line 12, with the following rewritten paragraph:

It is to be noted that, in the third modification, the refraction surfaces of the micro lens array 13[[,]] and the micro cylindrical lens array 13' ~~and~~ may be formed into a continuous curved surface shape or a step-like shape. Further, it is not restricted to a continuous curved surface or its multilevel approximation, and a split wavefront element can be constituted as a "kinoform" obtained by folding back a range of 0 to  $2\pi$  of a phase difference. Furthermore, the effect may be realized by a refractive index distribution of an optical material without giving the refraction surface to the split wavefront element. In this case, it is possible to use a prior art such as a photopolymer whose refractive index is modulated by a light intensity, ion exchange of glass, and others. Moreover, the split wavefront element may be realized by using a hologram or a diffraction optical element.

Please replace the paragraph at page 66, line 7-17, with the following rewritten paragraph:

Although the light intensity distribution can be calculated on a design stage, it is desirable to observe and confirm the light intensity distribution on the actual processed surface (exposed surface). In order to realize this, it is good enough to enlarge the processed surface by the optical system and input a result by an imaging element such as a CCD. When the light to be used is a an ultraviolet ray, since the optical system is restricted, it is possible to provide a fluorescent screen to the processed surface and convert the light into visible light.